L	Hits	Search Text	DB	Time stamp	
Number 33	1	6335267.pn.	USPAT	2004/05/06	
		_	USPAT;	12:59 2004/05/06	
34	9083	(cmp or polish or polishing or planarize or planarizing) with (edge or bevel or	US-PGPUB;	13:47	
		peripheral)	EPO; JPO	2004/05/06	
35	2830	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or	USPAT; US-PGPUB;	13:48	
i		peripheral)) and (etch or etching)	EPO; JPO		
36	2245	(((cmp or polish or polishing or planarize or planarizing) with (edge or	USPAT; US-PGPUB;	2004/05/06	
		bevel or peripheral)) and (etch or	EPO; JPO	13.10	
		etching)) and @ay<=2001	Manam.	2004/05/06	
37	1091	((((cmp or polish or polishing or planarize or planarizing) with (edge or	USPAT; US-PGPUB;	13:49	
		bevel or peripheral)) and (etch or	EPO; JPO		
		etching)) and @ay<=2001) and (slurry or abrasive)			
38	310	(((((cmp or polish or polishing or	USPAT;	2004/05/06	
		planarize or planarizing) with (edge or	US-PGPUB;	13:49	
		bevel or peripheral)) and (etch or etching)) and @ay<=2001) and (slurry or	EPO; JPO		
		abrasive)) and (wire or wiring)		0004/05/05	
39	241	<pre>((((((cmp or polish or polishing or planarize or planarizing) with (edge or</pre>	USPAT	2004/05/06	
		bevel or peripheral)) and (etch or			
		etching)) and @ay<=2001) and (slurry or			
		abrasive)) and (wire or wiring)) and @ay<=20010417			
40	9	("5152857" "5254830" "5374564"	USPAT	2004/05/06	
		"5494862" "5766065" "5928066" "5942445" "6312797" "6352927").PN.		13:51	
41	8	("4393628" "4466218" "5899738"	USPAT	2004/05/06	
		"6001447" "6045435" "6110021"		14:21	
42	1	"6121111" "6251215").PN. "6091130".PN.	USPAT	2004/05/06	
				14:26	
53	1	("6048763" "2002/0022936").PN.	USPAT	2004/05/06 15:07	
54	- 11	("4193226" "4811522" "5421769"	USPAT	2004/05/06	
		"5584746" "6010964" "6020262" "6171513" "6203408" "6340326"		15:08	
		"6344414" "6368968").PN.			
55	39545	(wire or wiring) same (pattern or	USPAT	2004/05/06 15:18	
56	25648	paterning) (wire or wiring) with (pattern or	USPAT	2004/05/06	
		paterning)	110030	15:18	
57	222	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or	USPAT	2004/05/06 15:18	
		peripheral)) and ((wire or wiring) with			
58	207	(pattern or paterning)) (((cmp or polish or polishing or	USPAT	2004/05/06	
38	207	planarize or planarizing) with (edge or	051111	16:01	
		bevel or peripheral)) and ((wire or			
		<pre>wiring) with (pattern or paterning))) and @ay<=2001</pre>			
59	4209	wiring with interconnect	USPAT	2004/05/06	
60	0	(wiring with interconnect) and	USPAT	16:01 2004/05/06	
00		semiconducotor		16:01	
61	2385	(wiring with interconnect) and	USPAT	2004/05/06	
62	2978	semiconductor wiring near4 interconnect	USPAT	2004/05/06	
			HCDAM	16:01	
63	1760	(wiring near4 interconnect) and semiconductor	USPAT	2004/05/06 16:02	
64	583	((wiring near4 interconnect) and	USPAT	2004/05/06	
65	398	semiconductor) and polishing (((wiring near4 interconnect) and	USPAT	16:02 2004/05/06	
65	396	semiconductor) and polishing) and copper		16:02	
Search Hi	story 5	5/6/04 4:44:43 PM Page 1			

(66	365	((((wiring near4 interconnect) and semiconductor) and polishing) and copper)	USPAT	2004/05/06 16:41
	67	8	and @ay<=2001 (("6059889") or ("5901399") or ("5868857") or ("5976267") or ("5874778")	USPAT	2004/05/06 16:41
-	-	29472	or ("6334229") or ("6309981") or ("6267649")).PN. (cmp or polish or polishing or planarize	USPAT	2004/05/06
-	-	12603	or planarizing) and (edge or pivot) ((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and	USPAT	2004/05/05 11:09
-	_	6238	semiconductor (((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or	USPAT	2004/05/05 11:09
-	_	1126	etching) and (mask or hard\$lmask) ((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or	USPAT	2004/05/05
	_	485	etching) and (mask or hard\$lmask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot)) ((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$lmask)) and	USPAT	2004/05/05 11:11
-	_	457	<pre>((cmp or polish or polishing or planarize or planarizing) with (edge or pivot)) (((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or</pre>	USPAT	2004/05/05 11:12
	_	284	planarize or planarizing) and (edge or	USPAT	2004/05/05 11:12
	-	145	pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive) (((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or	USPAT	2004/05/05 14:48
	_	9	etching) and (mask or hard\$lmask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive)	USPAT	2004/05/05 11:40
	-	3	"5982003" "6118152" "6294478").PN. (("6663468") or ("6596087") or	USPAT	2004/05/05
	-	1	("6563172")).PN. ("6379782").PN.	USPAT	12:57
	-	1	"6091130".PN.	USPAT	14:38 2004/05/05 12:57
	-	61	Iguchi-Manabu.in.	USPAT; JPO; DERWENT; IBM TDB	2004/05/05 14:38
	-	19	Iguchi-Manabu.in. and semiconductor	USPAT; JPO; DERWENT;	2004/05/05 14:38
	_	1	"6091130".PN.	IBM_TDB USPAT	2004/05/05 14:41

				0001/05/05
-	139	((((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$lmask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive)) not (((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$lmask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive))	USPAT	2004/05/05
-	10	("5409569" "6136708" "6162301" "6165956" "6261849" "6287477" "6294027" "6303551" "6322598" "6387190" "2001/0029104").PN.	USPAT	2004/05/05 15:01
-	1	Yoshihisa-Matsubara.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/05/05
_	103	Matsubara-Yoshihisa.in.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05
_	99	Matsubara-Yoshihisa.in. and semiconductor	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05
_	20	(Matsubara-Yoshihisa.in. and semiconductor) and polishing	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05
_	22	Takewaki-Toshiyuki.in.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05
_	4196	(cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)	USPAT	2004/05/05
_	1887	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001	USPAT	2004/05/05
	1217	<pre>(((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001) and (slurry or abrasive)</pre>	USPAT	2004/05/05 15:35
_	178	((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and (@ay<=2001) and (slurry or abrasive)) and (mask or hard\$lmask)	USPAT	2004/05/05 15:35

-	176	((((cmp or polish or polishing or	USPAT	2004/05/05
		planarize or planarizing) with (edge or		15:35
		bevel\$3)) and semiconductor and		
		@ay<=2001) and (slurry or abrasive)) and		
		(mask or hard\$1mask)) not ((((((cmp or		
		polish or polishing or planarize or		
		planarizing) and (edge or pivot)) and		
!	İ	semiconductor) and (etch or etching) and		
1		(mask or hard\$1mask)) and ((cmp or polish		
		or polishing or planarize or planarizing)		
		same (edge or pivot))) and (slurry or		
		abrasive)) not ((((((cmp or polish or		
	Į l	polishing or planarize or planarizing)		
		and (edge or pivot)) and semiconductor)		
	İ	and (etch or etching) and (mask or		
		hard\$1mask)) and ((cmp or polish or	i	
		polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and		1
		With (edge of pivot))) and eay(-2001) and		
		(slurry or abrasive))) or Matsubara-Yoshihisa.in.)		
	1424	(cmp or polish or polishing or planarize	USPAT	2004/05/05
_	1424	or planarizing) and (chamfer\$3)		15:42
_	1428	(cmp or polish or polishing or planarize	USPAT	2004/05/05
	1120	or planarizing) and (chamfer\$4)		15:42
_	428	((cmp or polish or polishing or planarize	USPAT	2004/05/05
		or planarizing) and (chamfer\$4)) and		15:42
		semiconductor		
_	301	(((cmp or polish or polishing or	USPAT	2004/05/05
		planarize or planarizing) and		15:42
		(chamfer\$4)) and semiconductor) and (etch		
		or etching)	110.70	2004/05/05
-	281	((((cmp or polish or polishing or	USPAT	15:42
		planarize or planarizing) and (chamfer\$4)) and semiconductor) and (etch		13.42
1		or etching)) and Gay<=2001		
	265	(((((cmp or polish or polishing or	USPAT	2004/05/05
-	263	planarize or planarizing) and		15:43
		(chamfer\$4)) and semiconductor) and (etch		
		or etching)) and @ay<=2001) not		
		(((((((cmp or polish or polishing or		
		planarize or planarizing) and (edge or		
		pivot)) and semiconductor) and (etch or		
		etching) and (mask or hard\$1mask)) and		
		((cmp or polish or polishing or planarize		
		or planarizing) same (edge or pivot)))		
		and (slurry or abrasive)) not (((((cmp		
		or polish or polishing or planarize or		
		planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and		
		(mask or hard\$1mask)) and ((cmp or polish		
		or polishing or planarize or planarizing)		
		with (edge or pivot))) and @ay<=2001) and		
		(slurry or abrasive))) or		
		(Matsubara-Yoshihisa.in. and		
		semiconductor) or ((((cmp or polish or		
		polishing or planarize or planarizing)		
		with (edge or bevel\$3)) and semiconductor		
		and @ay<=2001) and (slurry or abrasive))		
		and (mask or hard\$1mask)))	, , , , , , , , , , , , , , , , , , ,	2004/05/05
-	9	("5152857" "5254830" "5374564"	USPAT	2004/05/05 15:45
1		"5494862" "5766065" "5928066"		10.40
	17	"5942445" "6312797" "6352927").PN. ("4294651" "4372803" "4940510"	USPAT	2004/05/05
-	17	"5233218" "5389551" "5426073"	351111	15:48
		"5445706" "5449532" "5622875"		
		"5893982" "5945351" "6033997"		
		"6080675" "6099748" "6150969"		
		"6294469" "6335267" "2001/0014570"		
		"2001/0039101" "2002/0004305").PN.		